

Fig. 1

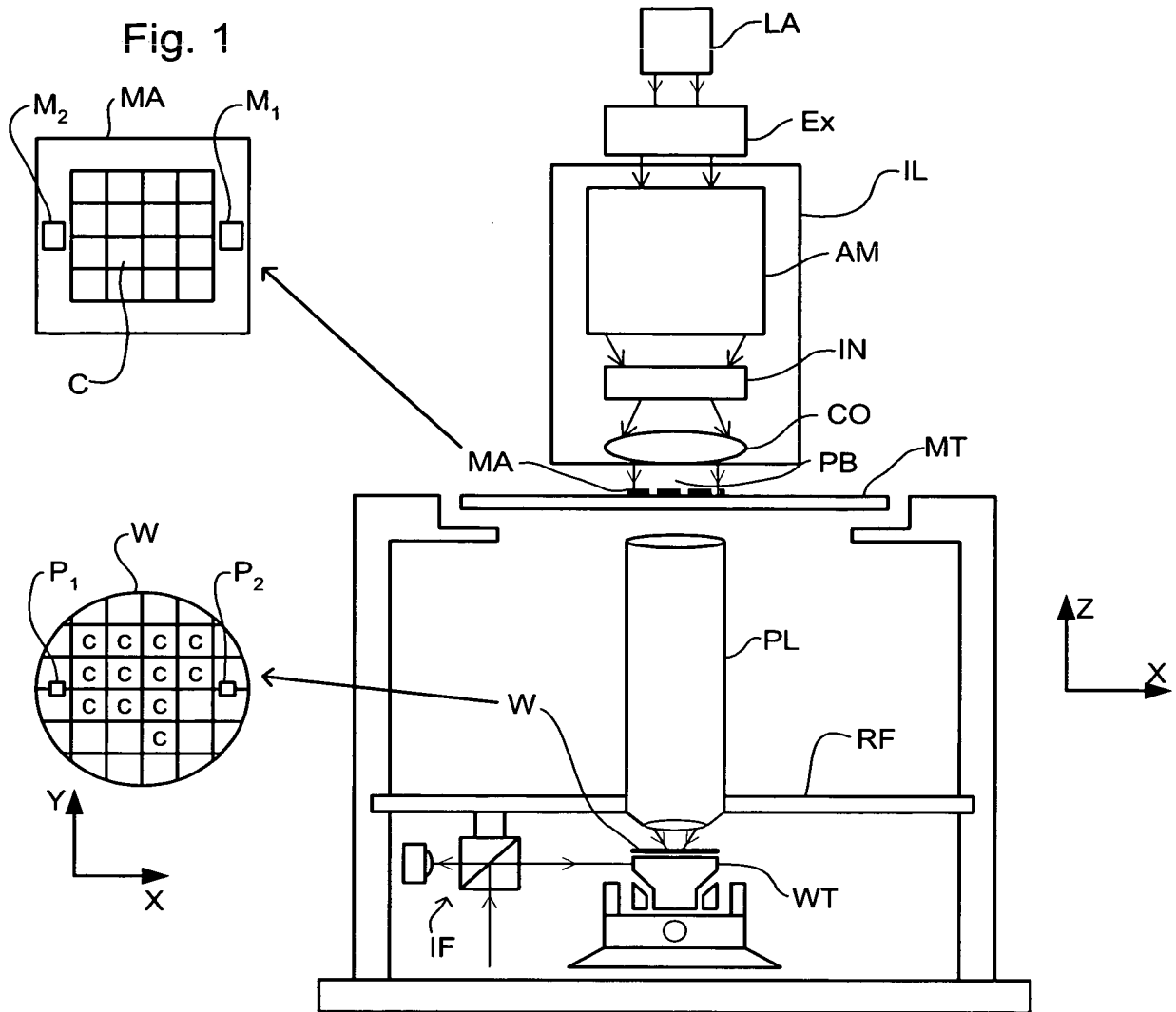


Fig. 2

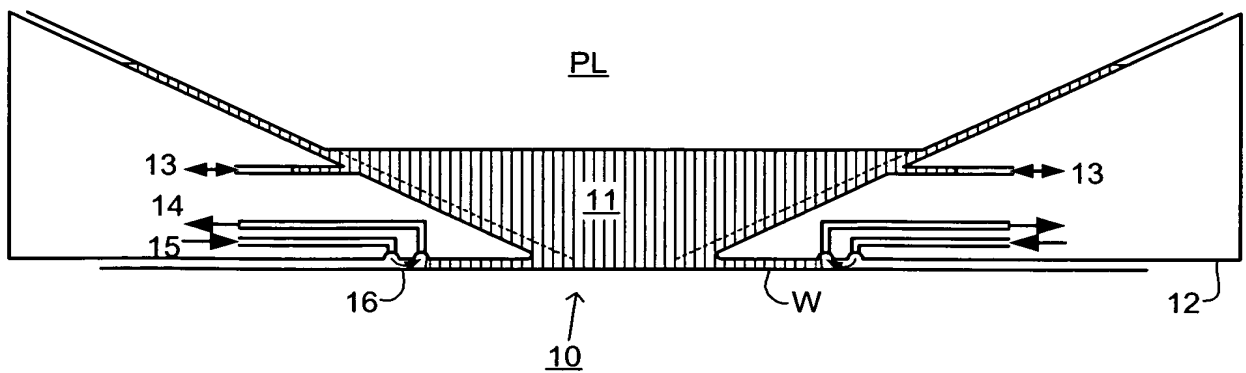
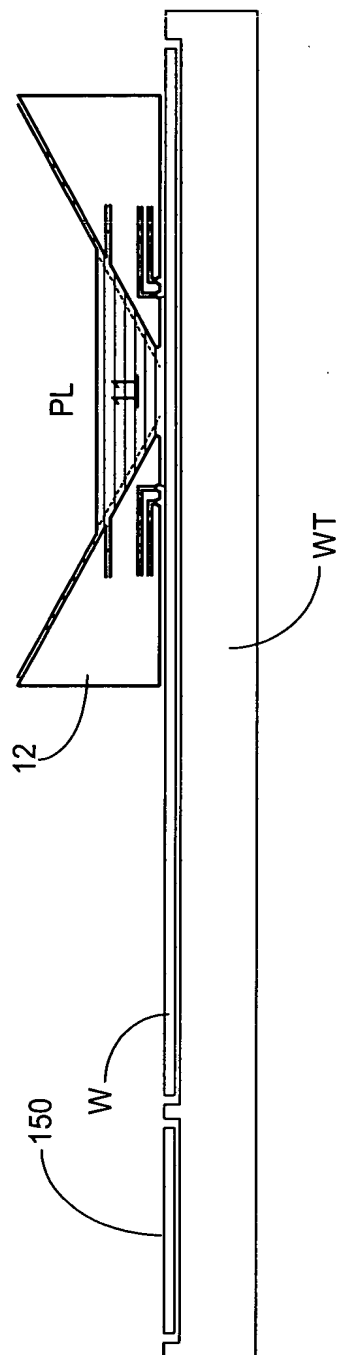


Fig. 4



A cross-sectional view of a semiconductor device. A central channel region is labeled **11**. On either side of the channel are side regions labeled **12**. A layer labeled **PL** is positioned above the channel and side regions. Below the channel, a layer labeled **150** is shown, with a sub-layer labeled **170** underneath it. A layer labeled **WT** is located below the **150** layer. On the left side, a stack of layers is labeled **17**. Two curved arrows, both labeled **160**, point from the side regions **12** towards the central channel **11**.

PILLSBURY WINTHROP LLP
MCLEAN, VIRGINIA

4/5

Fig. 7

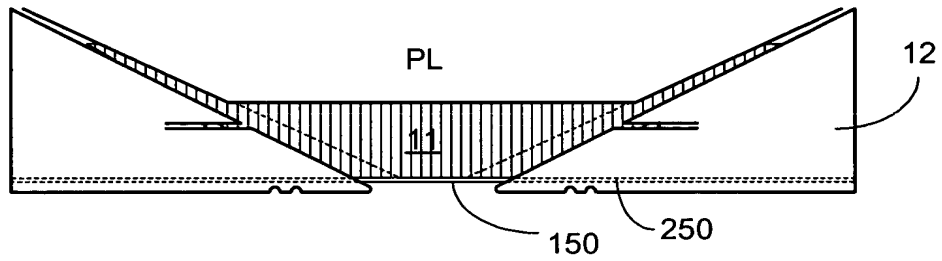
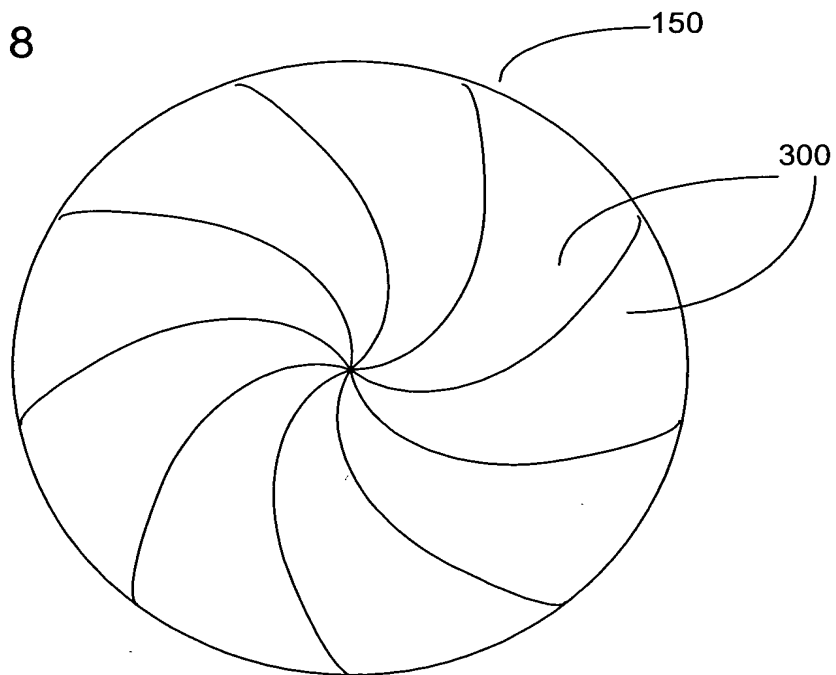


Fig. 8



PILLSBURY WINTHROP LLP
MCLEAN, VIRGINIA

5 / 5

Fig. 9

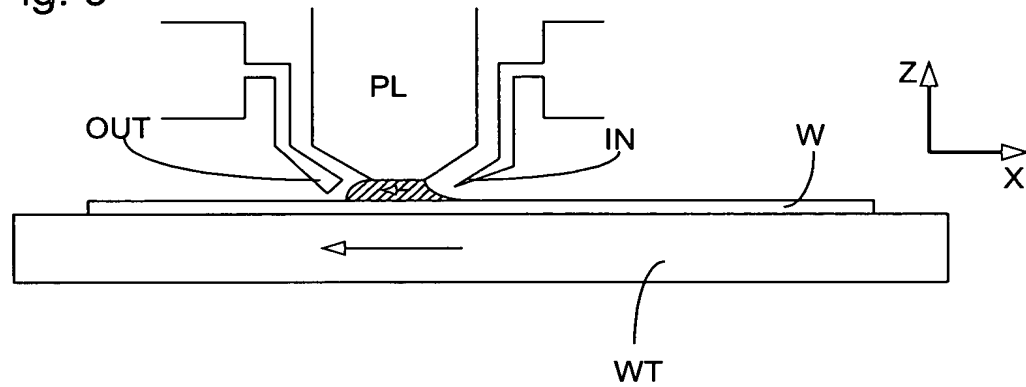


Fig. 10

